

# MR16: Schottky bridge rectifier plus freewheel diode

## Summary

Schottky Bridge and Freewheel diode for use in MR16 LED Drive Internal Ambient Temperature = 90°C MAX\*

 $V_R = 13.2 V_{RMS}$ ;  $I_F = 0.4 A_{AVG}$ ;  $I_R = 10 \mu A$ 

\*within MR16 circuit enclosure



This low leakage Schottky bridge and freewheel diode have been specifically designed for the MR16 LED driver solution alongside ZXLD1350E5 as described in Design Note DN86.

## **Key benefits**

· Compact surface mount solution and reduced component count in MR16 LED drive circuit

### **Features**

- Optimized bridge and freewheel diode for use in MR16 LED diode circuitry
- · Low VF and low reverse leakage current

## **Ordering information**

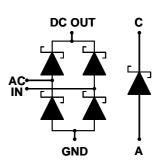
Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXSBMR16PT8TA	7	12	1000

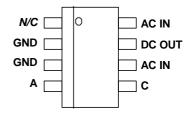
## **Device marking**

**ZXSB** MR16P



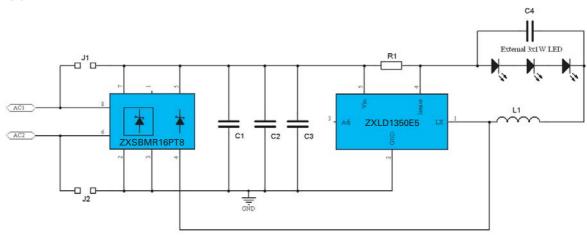
SM8





Pinout - top view

## **Application Schematic from DN86**



## **Absolute maximum ratings**

Parameter	Symbol	Value	Unit
Bridge	<u>.</u>		
Maximum repetitive reverse voltage	V <sub>RRM</sub>	40	V
Maximum RMS bridge input voltage	V <sub>RMS</sub>	13.2	V
Average rectified forward current <sup>(a)(b)</sup>	I <sub>F(AV)</sub>	0.4	Α
Peak repetitive forward current	I <sub>FPK</sub>	3.5	Α
Non repetitive forward current t=≤100µs t=≤10ms	I <sub>FSM</sub>	13 3.5	A A
Package			
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	1	W
Storage temperature range	Tstg	-55 to +150	°C
Junction temperature forward dissipation only	Tj	150	°C
Junction temperature reverse dissipation(a)(b)(c)	Tj	125	°C
MR16 LED internal ambient temperature <sup>(d)</sup>	T <sub>amb</sub>	90	°C

### Thermal characteristics

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	125	°C/W

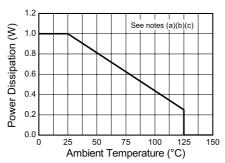
#### NOTES:

(a) For a bridge mounted on 1.6mm FR4 PCB with minimum copper pads and track dimensions in still air.

<sup>(</sup>b) Supply 12V RMS with capacitive bridge load.

<sup>(</sup>c) Maximum bridge operating junction temperature must be reduced with increased reverse bias voltage to maintain unconditional thermal stability.

<sup>(</sup>d) Refer to Design Note DN86



**Package Thermal Characteristic** 

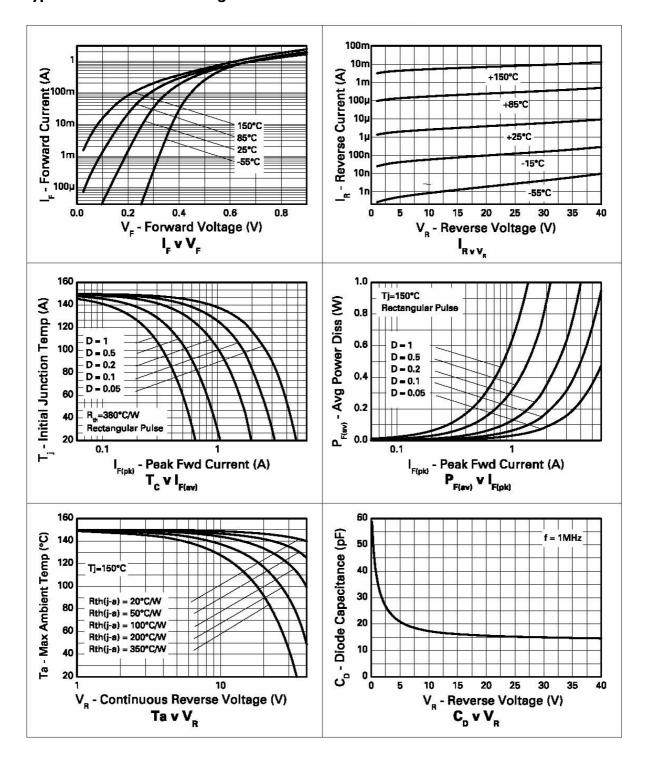
# **Electrical characteristics per diode** (at $T_{amb} = 25$ °C unless otherwise stated)

Schottky diode characteristics							
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Reverse breakdown voltage	V <sub>(BR)R</sub>	40			V	I <sub>R</sub> =200μA	
Forward voltage	V <sub>F</sub>		305	360	mV	I <sub>F</sub> =50mA <sup>(*)</sup>	
			355	410	mV	I <sub>F</sub> =100mA <sup>(*)</sup>	
			405	470	mV	I <sub>F</sub> =250mA <sup>(*)</sup>	
			485	550	mV	I <sub>F</sub> =500mA <sup>(*)</sup>	
			570	660	mV	I <sub>F</sub> =750mA <sup>(*)</sup>	
			640	750	mV	I <sub>F</sub> =1A <sup>(*)</sup>	
			415		mV	I <sub>F</sub> =500mA <sup>(*)</sup> ,T <sub>a</sub> = 100°C	
Reverse current	I <sub>R</sub>		6	10	μΑ	V <sub>R</sub> =30V	
			370		μΑ	$V_R=30V$ , $T_a=85$ °C	
Diode capacitance	C <sub>D</sub>		16		pF	f=1MHz,V <sub>R</sub> =30V	
Reverse recovery time Reverse recovery charge	t <sub>rr</sub> Q <sub>rr</sub>		3 210		ns pC	Switched from $I_F = 500 \text{mA}$ to $V_R = 5.5 \text{V}$ Measured @ $I_R$ 50 mA. di/dt = 500 mA/ns. Rsource = $6\Omega$ ; Rload = $10\Omega$	

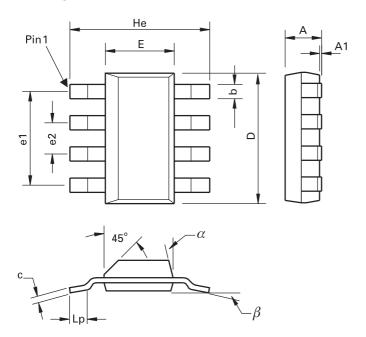
### NOTES:

(\*) Measured under pulsed conditions. Pulse width = 300 $\mu$ s; duty cycle  $\leq$ 2%.

## Typical characteristics single diode



# Package outline - SM8



DIM	N	/lillimete	rs		Inches		DIM	DIM Millimeters		Inches			
	Min.	Max.	Тур.	Min.	Max.	Тур.		Min.	Max.	Тур.	Min.	Max.	Тур.
Α	-	1.7	-	-	0.067	-	e1	-	-	4.59	-	-	0.1807
A1	0.02	0.1	-	0.0008	0.004	-	e2	-	-	1.53	-	-	0.0602
b	-	-	0.7	-	-	0.0275	He	6.7	7.3	-	0.264	0.287	-
С	0.24	0.32	-	0.009	0.013	-	Lp	0.9	-	-	0.035	-	-
D	6.3	6.7	-	0.248	0.264	-	α	-	15°	-	-	15°	-
E	3.3	3.7	-	0.130	0.145	-	β	-	-	10°	-	-	10°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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